

Reet Chaudhuri

List of Publications by Year in descending order

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Version: 2024-02-01

21
papers

560
citations

840585

11
h-index

839398

18
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21
all docs

21
docs citations

21
times ranked

529
citing authors

#	ARTICLE	IF	CITATIONS
1	A polarization-induced 2D hole gas in undoped gallium nitride quantum wells. <i>Science</i> , 2019, 365, 1454-1457.	6.0	106
2	High Breakdown Voltage in RF AlN/GaN/AlN Quantum Well HEMTs. <i>IEEE Electron Device Letters</i> , 2019, 40, 1293-1296.	2.2	79
3	Prospects for Wide Bandgap and Ultrawide Bandgap CMOS Devices. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 4010-4020.	1.6	73
4	Gate-Recessed E-mode p-Channel HFET With High On-Current Based on GaN/AlN 2D Hole Gas. <i>IEEE Electron Device Letters</i> , 2018, 39, 1848-1851.	2.2	62
5	Next generation electronics on the ultrawide-bandgap aluminum nitride platform. <i>Semiconductor Science and Technology</i> , 2021, 36, 044001.	1.0	42
6	First RF Power Operation of AlN/GaN/AlN HEMTs With >3 A/mm and 3 W/mm at 10 GHz. <i>IEEE Journal of the Electron Devices Society</i> , 2021, 9, 121-124.	1.2	33
7	Molecular beam epitaxial growth of scandium nitride on hexagonal SiC, GaN, and AlN. <i>Applied Physics Letters</i> , 2019, 115, .	1.5	24
8	GaN/AlN Schottky-gate p-channel HFETs with InGaN contacts and 100 mA/mm on-current. , 2019, , .		22
9	Wurtzite phonons and the mobility of a GaN/AlN 2D hole gas. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	19
10	Polarization-induced 2D hole gases in pseudomorphic undoped GaN/AlN heterostructures on single-crystal AlN substrates. <i>Applied Physics Letters</i> , 2021, 119, .	1.5	15
11	GaN/AlN p-channel HFETs with $I_{\text{max}} > 420$ mA/mm and ~ 20 GHz f_{T} / f_{MAX} . , 2020, , .		13
12	Molecular Beam Epitaxy Growth of Large Area GaN/AlN 2D Hole Gas Heterostructures. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900567.	0.7	12
13	High-conductivity polarization-induced 2D hole gases in undoped GaN/AlN heterojunctions enabled by impurity blocking layers. <i>Journal of Applied Physics</i> , 2021, 130, 025703.	1.1	12
14	Terahertz spectroscopy of an electron-hole bilayer system in AlN/GaN/AlN quantum wells. <i>Applied Physics Letters</i> , 2017, 111, .	1.5	9
15	In Situ Crystalline AlN Passivation for Reduced RF Dispersion in Strained p-Channel AlN/GaN/AlN High Electron Mobility Transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2022, 219, 2100452.	0.8	9
16	X-band epi-BAW resonators. <i>Journal of Applied Physics</i> , 2022, 132, .	1.1	8
17	Very High Density ($>10^{14}$ cm ⁻²) Polarization-Induced 2D Hole Gases Observed in Undoped Pseudomorphic InGaN/AlN Heterostructures. <i>Advanced Electronic Materials</i> , 2022, 8, .	2.6	6
18	Electric Fields and Surface Fermi Level in Undoped GaN/AlN Two-Dimensional Hole Gas Heterostructures. <i>Physica Status Solidi - Rapid Research Letters</i> , 2021, 15, 2000573.	1.2	5

#	ARTICLE	IF	CITATIONS
19	Large Signal Response of AlN/GaN/AlN HEMTs at 30 GHz. , 2021, , .		5
20	<i>(Invited)</i> GaN-Based Multiple 2DEG Channel BRIDGE (Buried Dual Gate) HEMT Technology for High Power and Linearity. ECS Transactions, 2019, 92, 103-108.	0.3	4
21	Quantitative scanning microwave microscopy of 2D electron and hole gases in AlN/GaN heterostructures. Applied Physics Letters, 2022, 120, 012103.	1.5	2